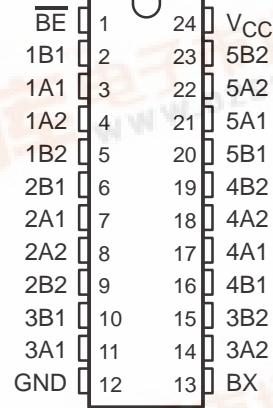


SN74CBTLV3383 LOW-VOLTAGE 10-BIT FET BUS-EXCHANGE SWITCH

SCDS047D – MARCH 1998 – REVISED NOVEMBER 1999

- Functionally Equivalent to QS3383 and QS3L383
- 5- Ω Switch Connection Between Two Ports
- Isolation Under Power-Off Conditions
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Package Options Include Shrink Small-Outline (DBQ), Thin Very Small-Outline (DGV), Small-Outline (DW), and Thin Shrink Small-Outline (PW) Packages

DBQ, DGV, DW, OR PW PACKAGE
(TOP VIEW)

description

The SN74CBTLV3383 provides ten bits of high-speed bus switching or exchanging. The low on-state resistance of the switch allows connections to be made with minimal propagation delay.

The device operates as a 10-bit bus switch or a 5-bit bus exchanger, which provides swapping of the A and B pairs of signals. The bus-exchange function is selected when BX is high and \overline{BE} is low.

The SN74CBTLV3383 is characterized for operation from -40°C to 85°C .

FUNCTION TABLE

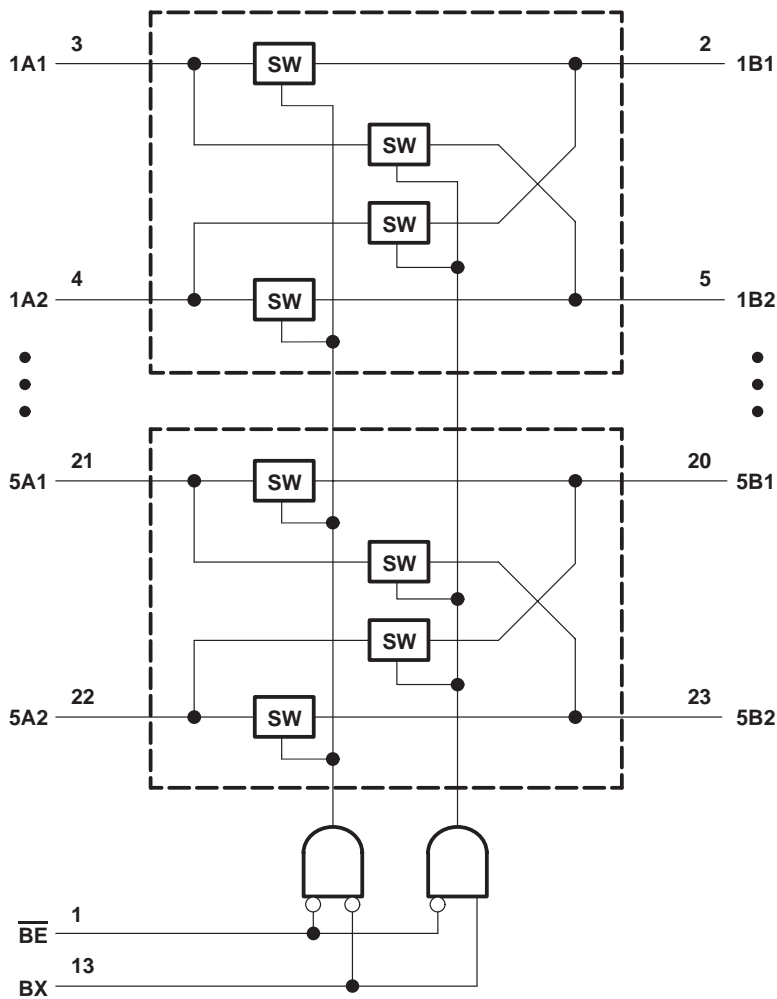
INPUTS		INPUTS/OUTPUTS	
\overline{BE}	BX	1A1–5A1	1A2–5A2
L	L	1B1–5B1	1B2–5B2
L	H	1B2–5B2	1B1–5B1
H	X	Z	Z

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

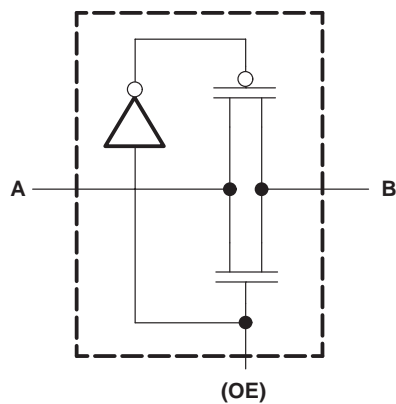
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logic diagram (positive logic)



simplified schematic, each FET switch



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC}	−0.5 V to 4.6 V
Input voltage range, V_I (see Note 1)	−0.5 V to 4.6 V
Continuous channel current	128 mA
Input clamp current, I_{IK} ($V_{I/O} < 0$)	−50 mA
Package thermal impedance, θ_{JA} (see Note 2): DBQ package	61°C/W
DGV package	86°C/W
DW package	46°C/W
PW package	88°C/W
Storage temperature range, T_{Stg}	−65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with JEDEC 51.

recommended operating conditions (see Note 3)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2.3	3.6	V
V _{IH}	High-level control input voltage	V _{CC} = 2.3 V to 2.7 V	1.7		V
		V _{CC} = 2.7 V to 3.6 V	2		
V _{IL}	Low-level control input voltage	V _{CC} = 2.3 V to 2.7 V		0.7	V
		V _{CC} = 2.7 V to 3.6 V		0.8	
T _A	Operating free-air temperature		−40	85	°C

NOTE 3: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP‡	MAX	UNIT
V _{IK}		V _{CC} = 3 V, I _I = −18 mA				−1.2	V
I _I		V _{CC} = 3.6 V, V _I = V _{CC} or GND				±1	μA
I _{off}		V _{CC} = 0, V _I or V _O = 0 to 3.6 V				10	μA
I _{CC}		V _{CC} = 3.6 V, I _O = 0, V _I = V _{CC} or GND				10	μA
ΔI _{CC} §	Control inputs	V _{CC} = 3.6 V, One input at 3 V, Other inputs at V _{CC} or GND				300	μA
C _i	Control inputs	V _I = 3 V or 0				3.5	pF
C _{IO} (OFF)		V _O = 3 V or 0, BE = V _{CC}				13.5	pF
r _{on} ¶		V _{CC} = 2.3 V, TYP at V _{CC} = 2.5 V	V _I = 0	I _I = 64 mA	5	8	Ω
				I _I = 24 mA	5	8	
		V _I = 1.7 V, I _I = 15 mA		27	40		
		V _{CC} = 3 V	V _I = 0	I _I = 64 mA	5	7	
				I _I = 24 mA	5	7	
			V _I = 2.4 V, I _I = 15 mA		10	15	

‡ All typical values are at $V_{CC} = 3.3\text{ V}$ (unless otherwise noted), $T_A = 25^\circ\text{C}$.

§ This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.

1 Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

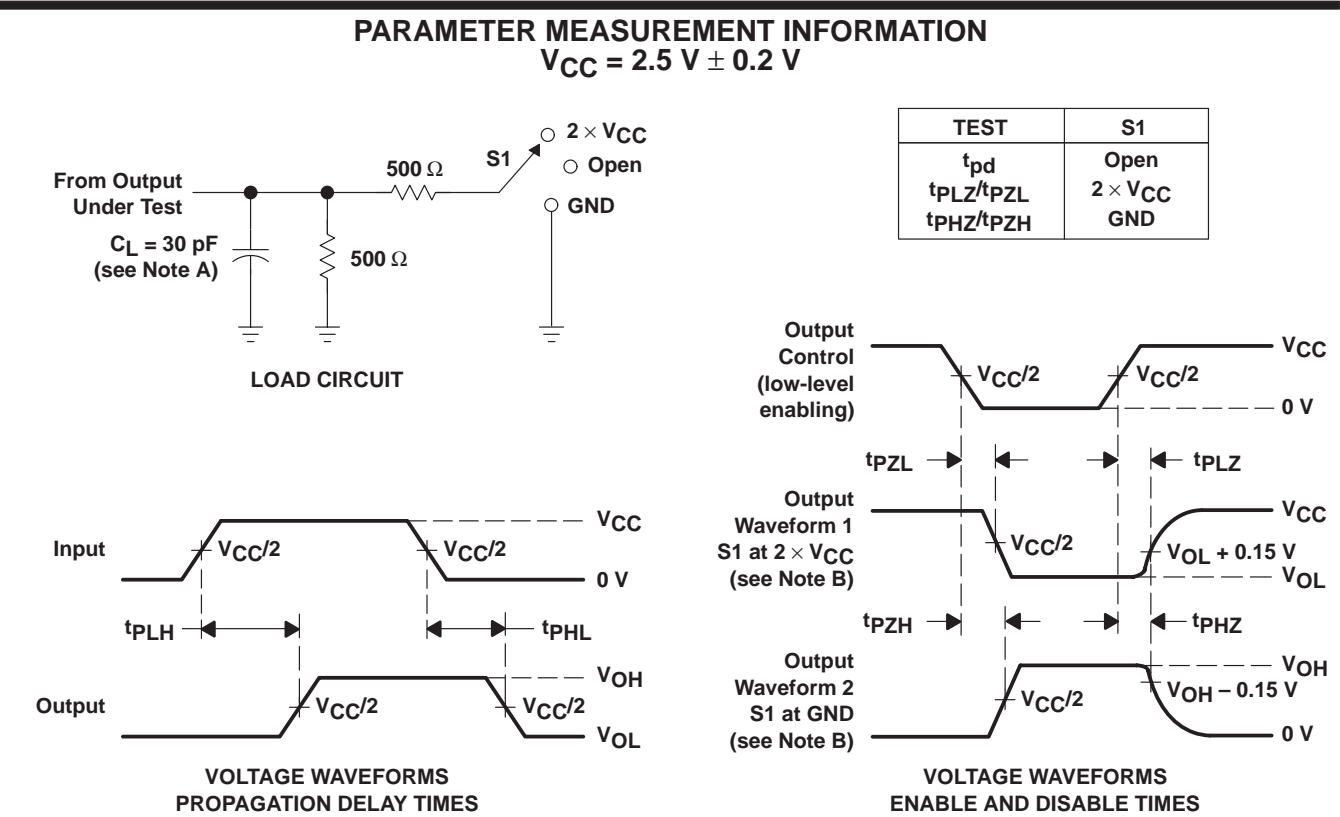
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switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	
t _{pd} [†]	A or B	B or A		0.15		0.25	ns
t _{pd}	BX	A or B	1.5	5.8	1.5	4.7	ns
t _{en}	$\overline{\text{BE}}$	A or B	1.5	5.3	1.5	4.7	ns
t _{dis}	$\overline{\text{BE}}$	A or B	1	6	1	6	ns

[†] The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
 - F. t_{PZL} and t_{PZH} are the same as t_{en}.
 - G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

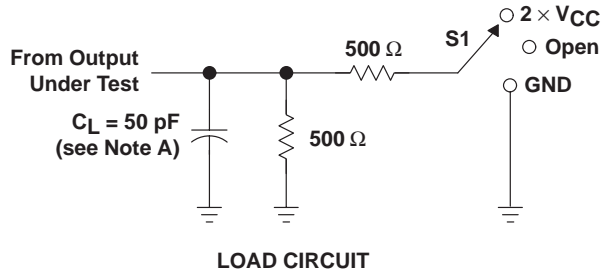
SN74CBTLV3383

LOW-VOLTAGE 10-BIT FET BUS-EXCHANGE SWITCH

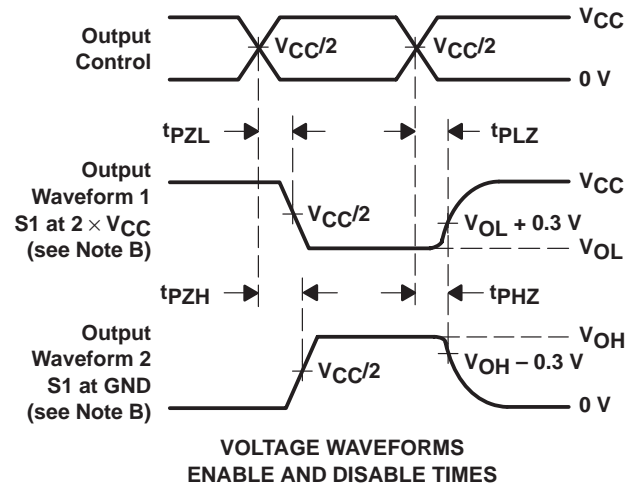
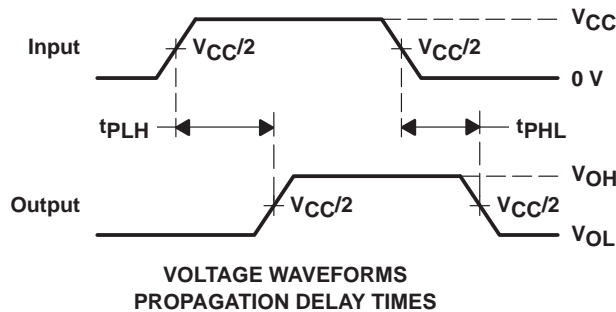
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PARAMETER MEASUREMENT INFORMATION

$$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$$



TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	GND



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .

Figure 2. Load Circuit and Voltage Waveforms

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